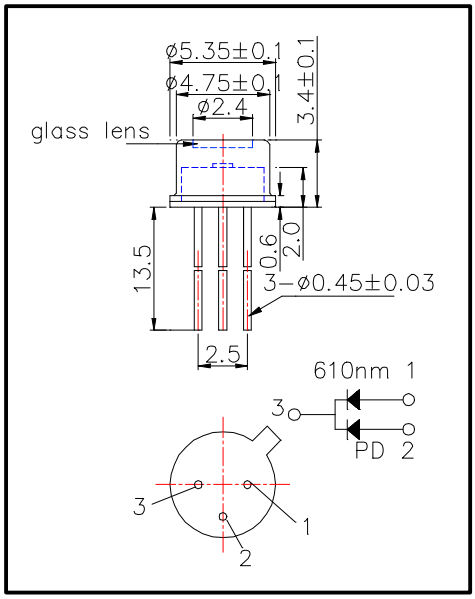
Preliminary

L525/PD010-35D52

Metal can sealed PD monitering high power LED

L525/PD010-35D52 consists of a InGaN LED 525nm and a Si-PD mounted onTO-18 stem hermetically sealed with a glass flat can, and is designed to moniter reflected light through detector for controlling its own output power

Outer dimension (Unit: mm)



Specifications

1) Product Name	LED Lamp with PD Monitor
2) Type No.	L525/PD010-35D52
3) Chip	
(1) Chip material	InGaN and Si(PIN)
(2) Peak wavelength	525nm
4) Package	
(1) Stem	**f** 5mm TO-18
(2) Lens	Metal Can (Gold Plate)

Absolute Maximum Ratings [Ta=25°C]

Device	Item	Symbol	Maximum Rated	Unit
LED	Power Dissipation	P_D	120	mW
LED	Forward Current	I_F	30	mA
LED	Pulse Forward Current	I_{FP}	-	A
LED	Reverse Voltage	V_R	5	V
PD	Reverse Voltage	V_R	100	V
	Operating Temperature	T_{OPR}	-20 ~ +85	°C
	Storage Temperature	T_{STG}	-30 ~ +95	°C
	Soldering Temperature	T_{SOL}	260	°C

‡ Soldering condition: Soldering condition must be completed within 3 seconds at 250°C

Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V_F	I_F=20mA		3.5	4.3	V
Reverse Current	I_R	V_R=5V			10	uA
Total Radiated Power	P_O	I_F=20mA		2.0		mW
Radiant Intensity	I_E	I_F=20mA		-		mW/sr
Peak Wavelength	**l** $_P$	I_F=20mA	515	525	535	nm
Half Width	**D l**	I_F=20mA		40		nm
Viewing Half Angle	**Q** $_{1/2}$	I_F=20mA		±55		deg.
Rise Time	tr	I_F=20mA		-		ns
Fall Time	tf	I_F=20mA		-		ns
Output Current	I_L	V_R=0V		55		uA
Dark Current	I_D	V_R=10V			10	nA

‡ Total Radiated Power is measured by Photodyne #500

EPITEX INC. : 4, Nishiaketa-Cho, Higashi-Kujyou, Minami-Ku, Kyoto, Japan
Tel.: ++81-75-682-2338 Fax: ++81-75-682-2267
e-mail: sales-dep@epitex.com http://www.epitex.com